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High Power Wafertest – How to keep the temperature under control



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CTO

Aug. 30 – Sep. 1, 2021

Agenda

- 1. Introduction of different high power scenarios**
- 2. Background – Market outlook and motivation**
- 3. Thermal challenges for each scenario**
- 4. Possible solutions for each scenario**
- 5. Summary**
- 6. Outlook**

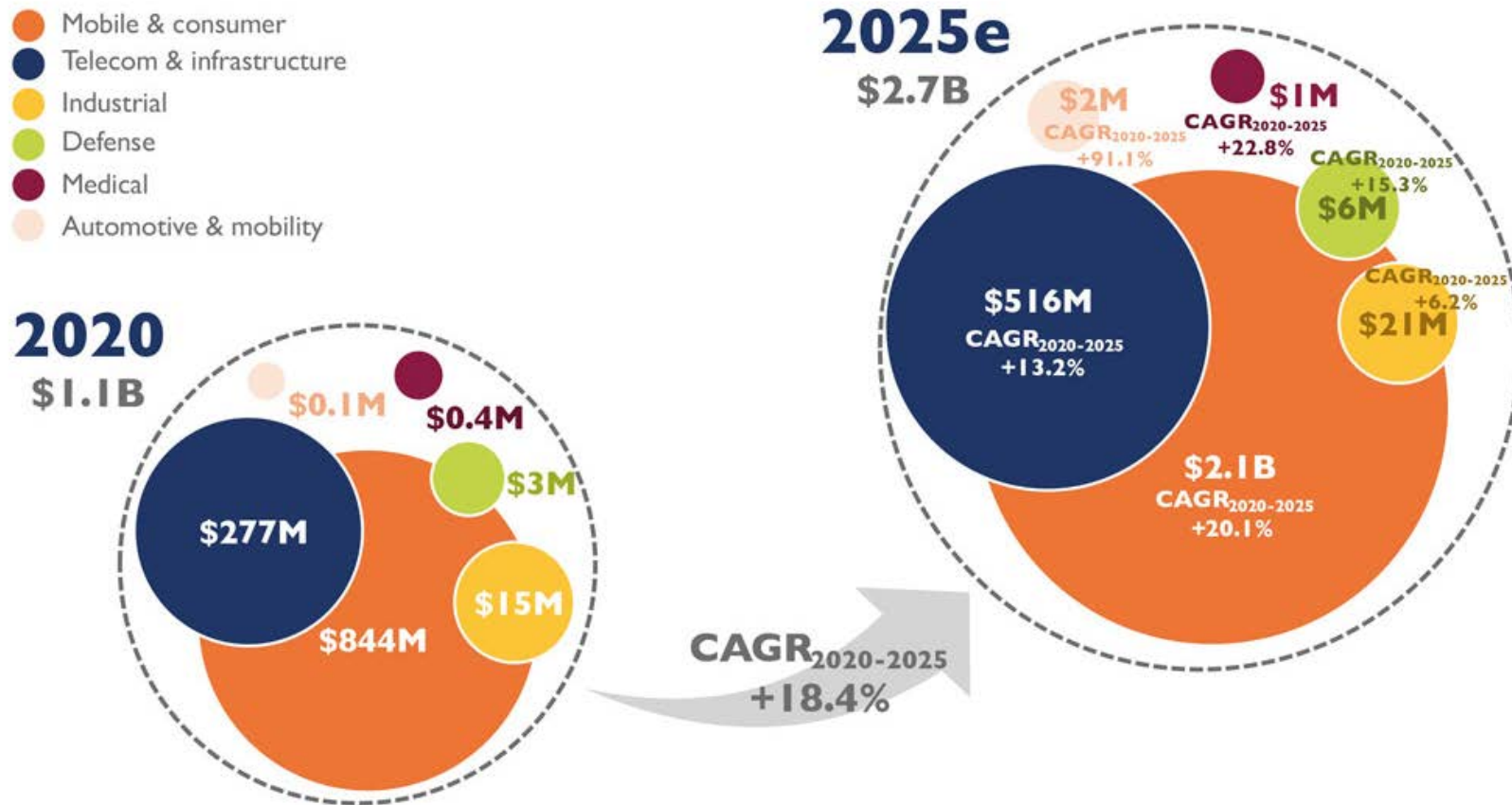
“High Power” – one term for different test scenarios

- 1. High voltage/High current/Short pulse test (HV/HC)**
- 2. Low voltage/High current per device/Single or low number of parallel DUT short screening test (Hi-Wattage)**
- 3. Low voltage/Low current per device/High number of parallel DUT/Full wafer contact (FWC)**

**One common challenge:
Accurate temperature regulation of DUT**

Market Outlook

(Source: VCSELS - Market and Technology Trends 2020 report, Yole Développement, 2020)

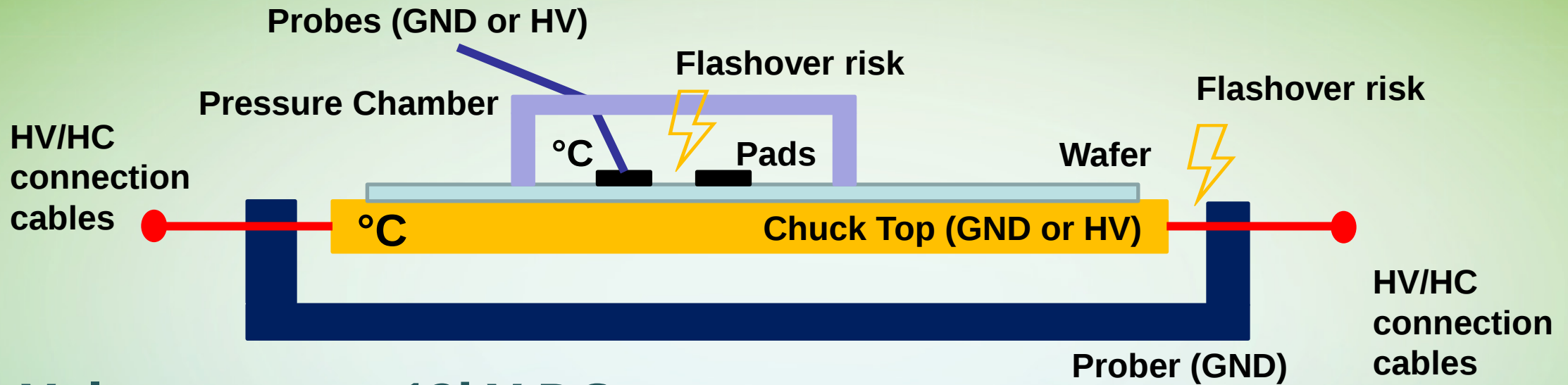


VCSEL

Motivation

- Major topics such as renewable energies, cloud computing, big data and electromobility would be inconceivable without them
- As with all semiconductor devices there is a trend to test early: means wafer probing
- As a thermal chuck manufacturer, we are focusing on temperature maintainance and accuracy under these special conditions

Typical HV – HC Test Set-up



- Voltages up to 12kV DC
- Current up to 600A
- Pulsed tests
- Spark suppression techniques are used (low conducting gases, pressurized chambers)

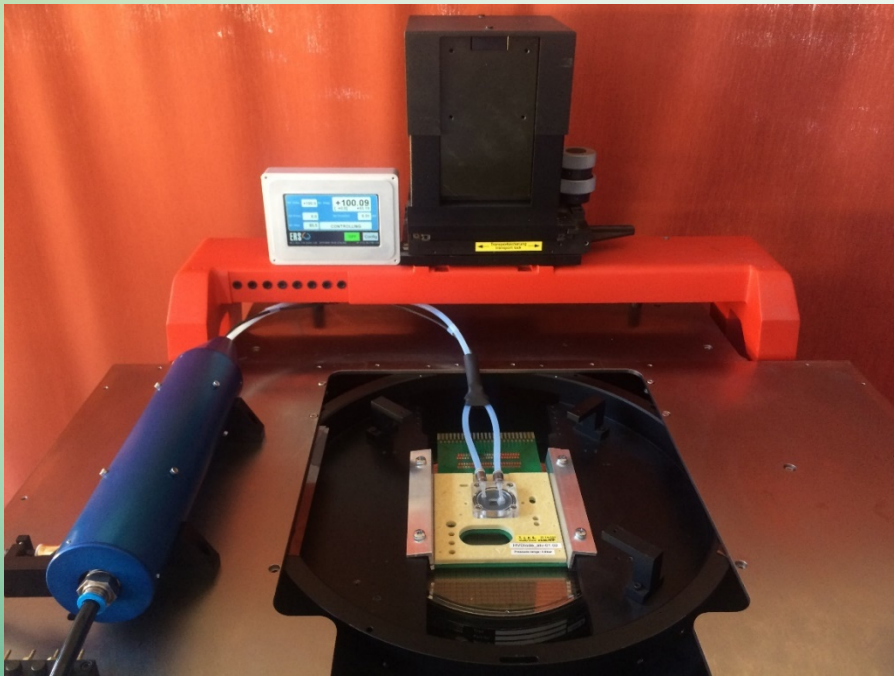
Products: IGBT, MOSFET, HV Diodes,

HV – HC Test Thermal Challenges

- CDA pressurized probe cards cause huge temperature offset at high temperature test
- Flashover risk at chuck and surrounding
- Wafer backside contact
- Very high temperature required for new materials (SiC, GaN)
- High voltage isolation layers needed, bad thermal conductivity

Solution for Temperature Offset Caused by CDA Pressurized Probe Cards

- **ATCM (Air Temperature Control Module)**



- Controls Temperature, Flow and Pressure of the CDA
- Usable up to +300°C
- Connected to chuck temperature controller with automatic offset algorithm



HV/HC Test - ATCM Performance

w/o ATCM

Chuck Temperature (°C)	CDA airflow (l/min)	DUT Temperature (°C)	Temperature Offset (°C)
60	60	50	-10
80	60	65	-15
100	60	80	-20
100	100	51	-49

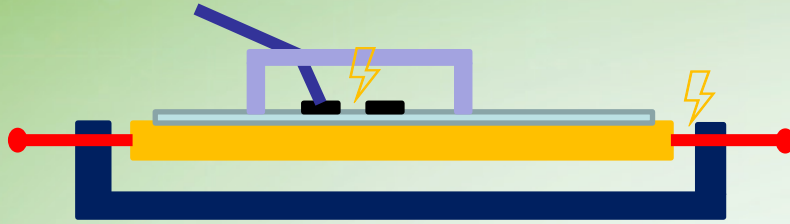
- Almost 50°C (!) offset

with ATCM

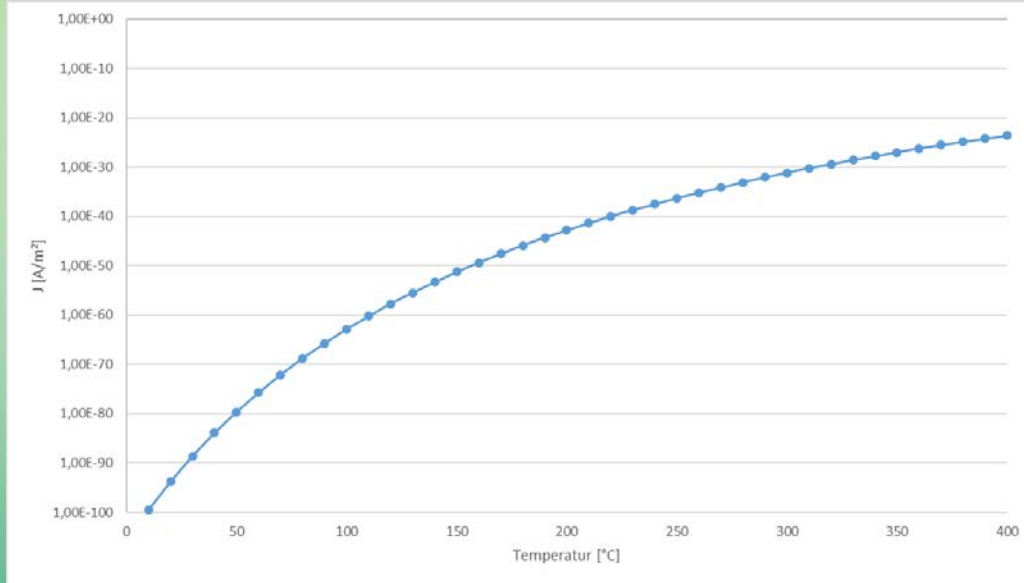
Chuck Temperature (°C)	Pressure (bar)	CDA airflow (l/min)	DUT Temperature (°C)	Temperature Offset (°C)
100	2	50	100	0
100	4	50	98,6	-1,4
100	4	75	99	-1
100	4	83	100	0
100	4	100	100,6	0,6
100	6	130	97	-3

- Offset clearly below 5°C
- Automatic adaption to even higher air flow

Flashover Risk in Dependency to Temperature



Flashover risk points



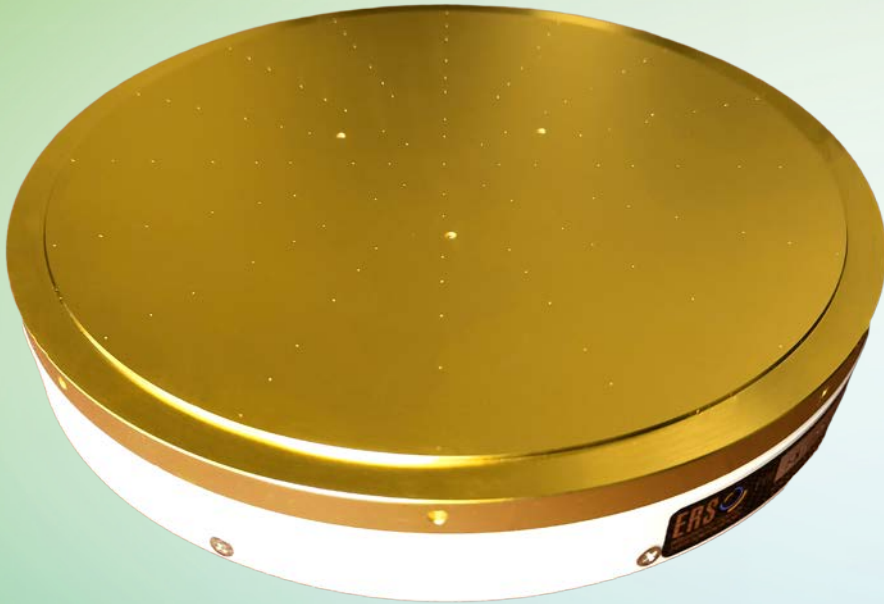
Current Density over Temperature

Gas Properties

Gas	$(E/p)_0$	c
	$\frac{\text{kV}}{\text{bar}\cdot\text{mm}}$	$\frac{\text{kV}}{(\text{bar}\cdot\text{mm})^{1/2}}$
SF_6	8,80	0,27
	6,61	2,19
CO_2	3,21	5,88
Luft	1,85	3,87
	2,43	2,01
	2,44	2,12
N_2	2,44	4,85
H_2	1,01	2,42

- Flashover risk significantly raises with higher temperature
- Air gaps have to be sufficient
- Other gases than air may help – but: environmental concerns have to be taken into account

Typical HV/HC High Temperature Chuck

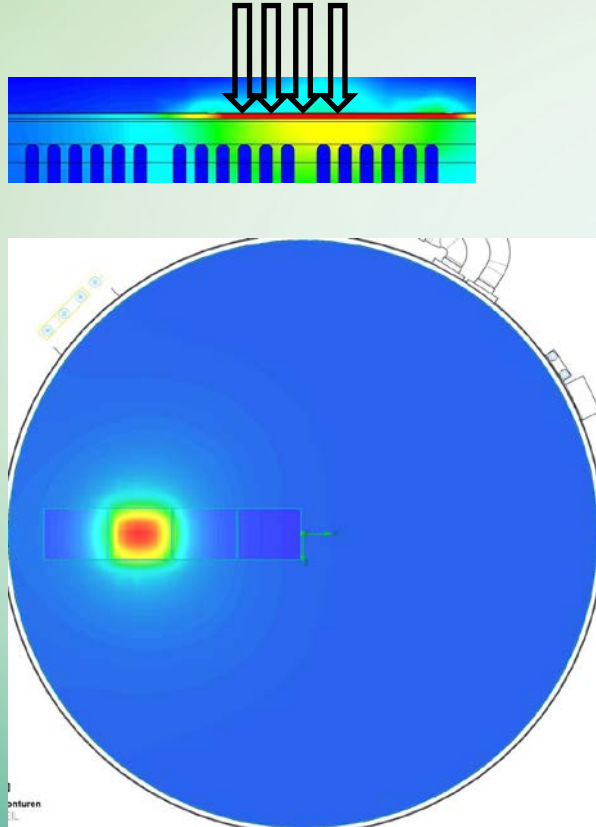


- Up to 12kV insulated chuck top
- Up to 3kV low leakage triaxial set up
- Thermally optimized and fully integrated insulation components
- Low resistance gold surface with special vacuum design
- Thermally designed HC connection points to the chuck top
- Ultra High Temperature configurations available for GaN, SiC, etc. wafers



Typical High Wattage Test Set up

Power Input >500W per die



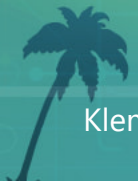
- **Single chip is tested with low voltage and high current**
- **A high-density power load is applied to the DUT**
- **High temperature rise needs to be addressed**
- **Temperature uniformity over the 300mm surface must be ensured under load**
- **Products are typically CPU, GPU**

High Wattage Test Thermal Challenges

- High wattage density needs high dissipation capability from the chuck underneath the wafer
- Cutting edge devices generating high wattage to be removed by the chuck and chiller
- Thermal resistance between wafer and chuck creates a temperature offset
- Thermal conditions for the DUT needs to be the same independent of the die's position on the wafer

Solution for High Wattage Dissipation

- **Chuck system combines multi sensor sections in the chuck with new liquid heat exchanger**
- **Thermal controller software controls temperature independently of DUT location**
- **New heat exchanger inside the chuck eliminates bottleneck for powerful liquid chiller**
- **Modular chiller concept to adapt on dissipation and temperature range**



High Wattage Dissipation

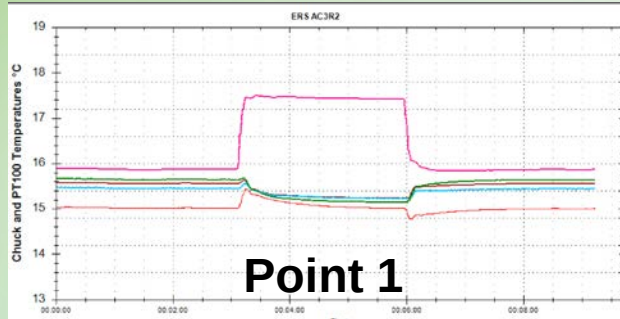
Measurement Set up



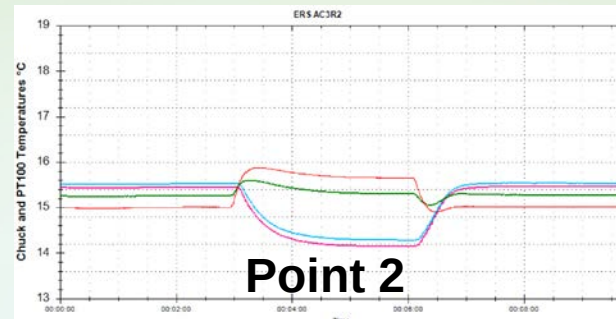
- Data taken at 9 different sections of the chuck
- Power density is 150W on 15mm x 15mm
- Chuck set point is +15°C
- Temperature is measured inside the chuck and also directly beside the DUT with extra sensor

High Wattage Dissipation Data

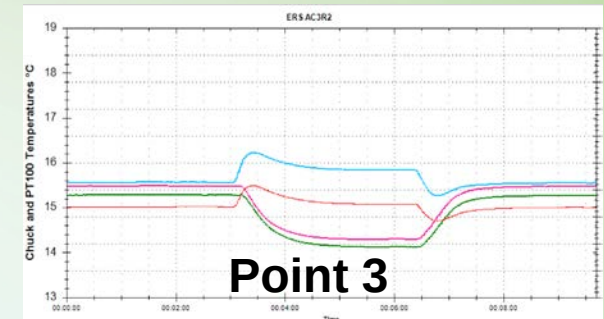
Data of 9 points, sensors inside the chuck:



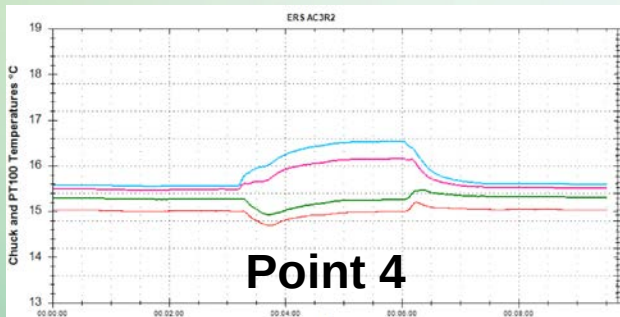
Point 1



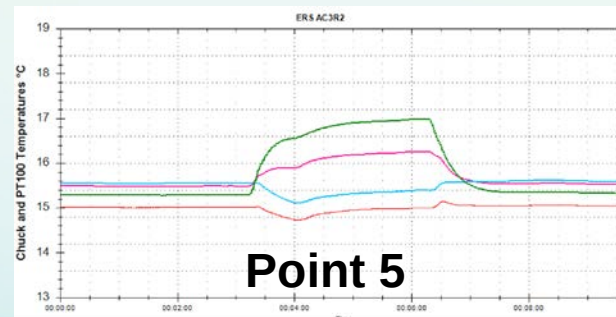
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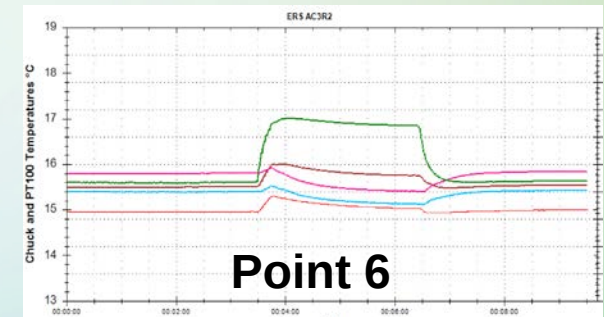
Point 3



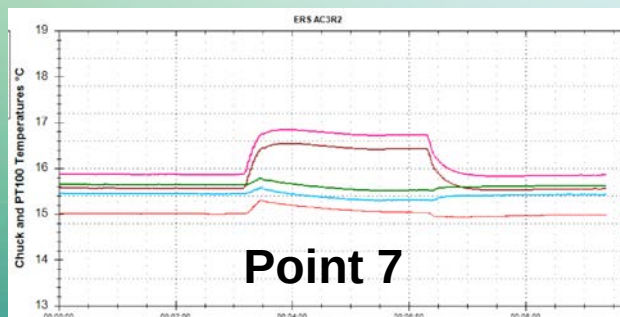
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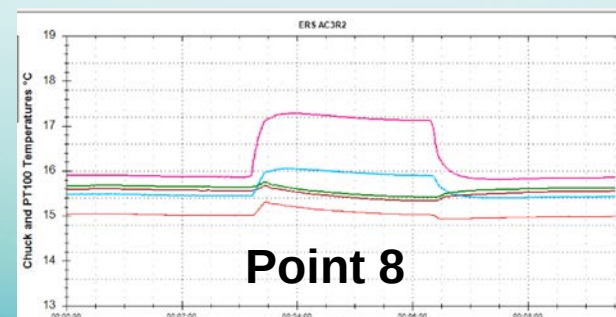
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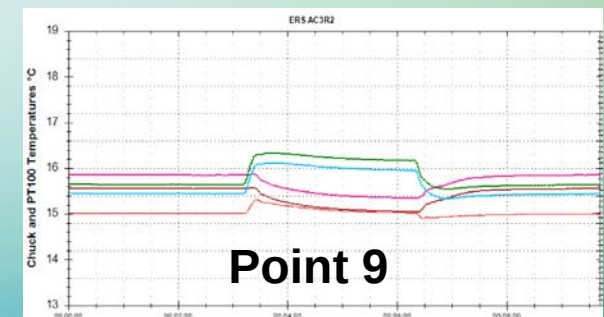
Point 6



Point 7



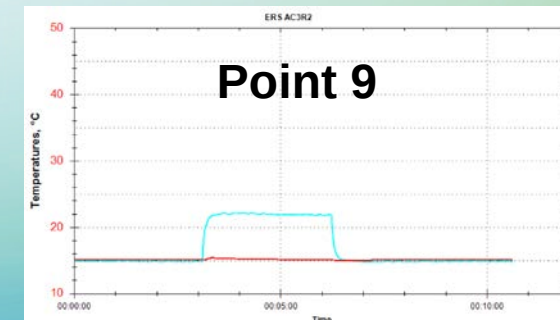
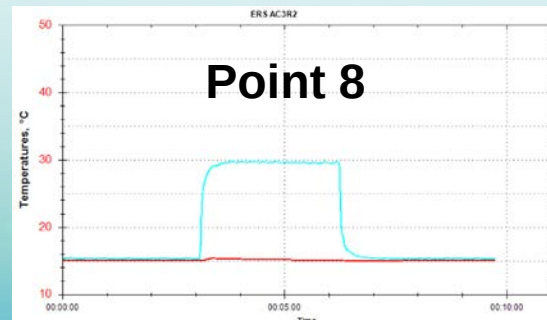
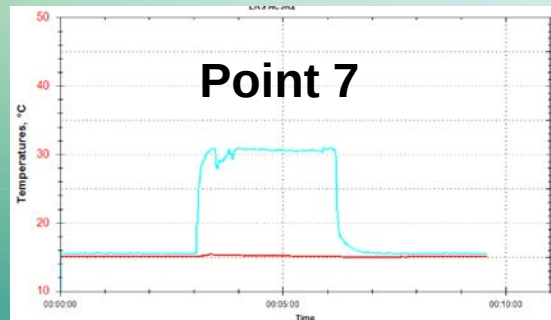
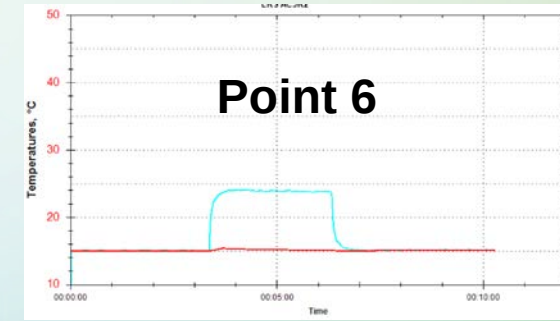
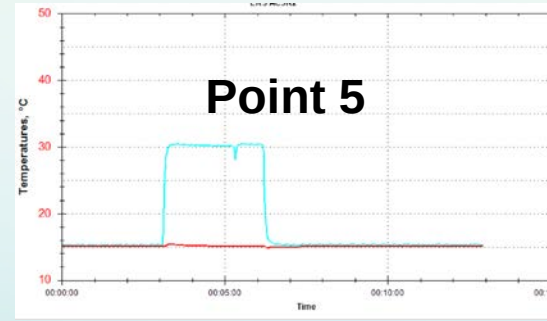
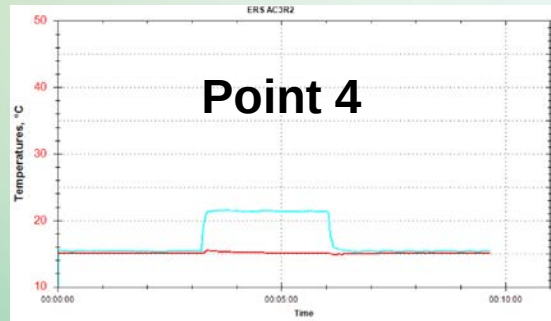
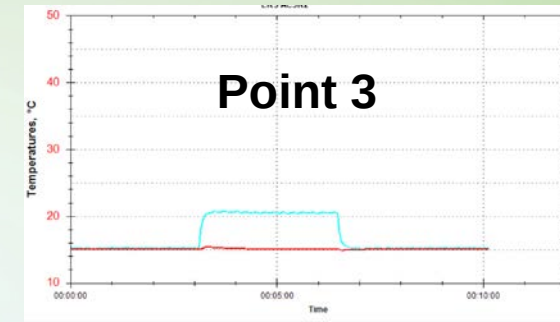
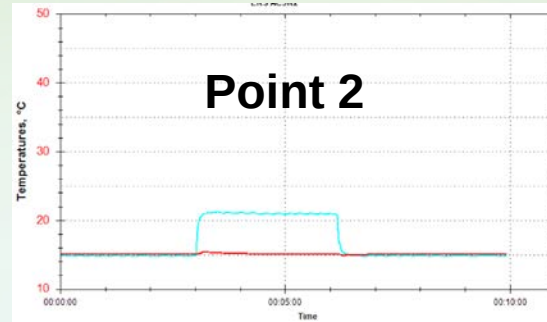
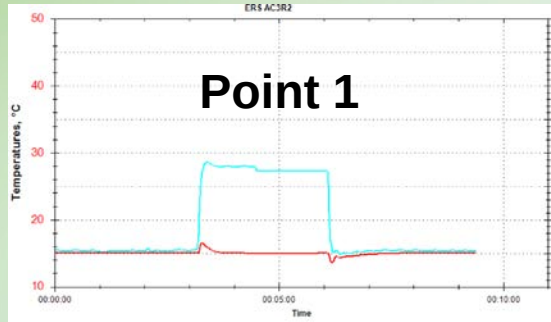
Point 8



Point 9

High Wattage Dissipation Data

Data of 9 points, extra Sensor:



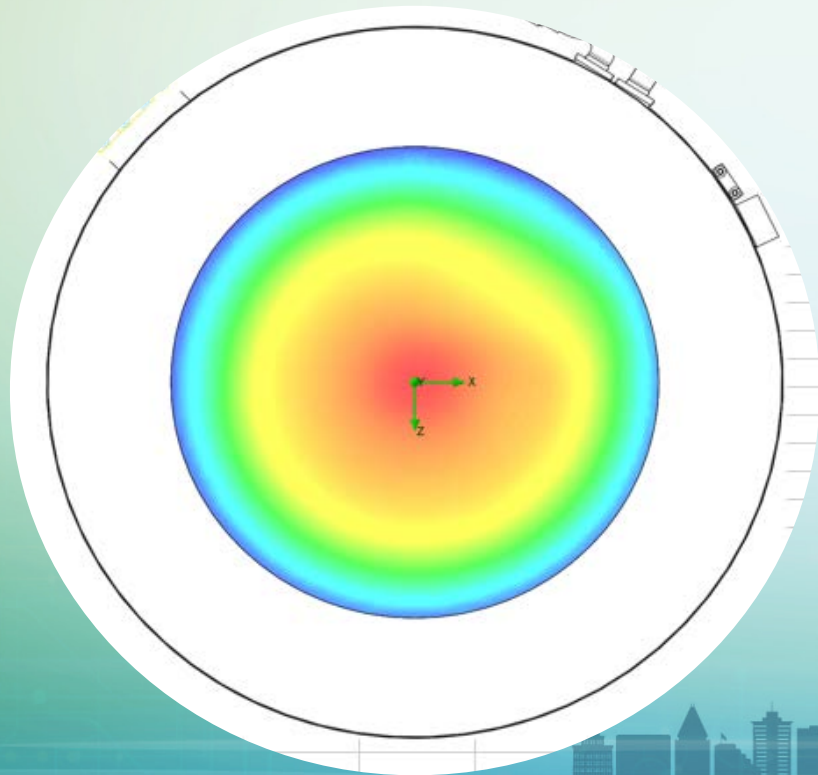
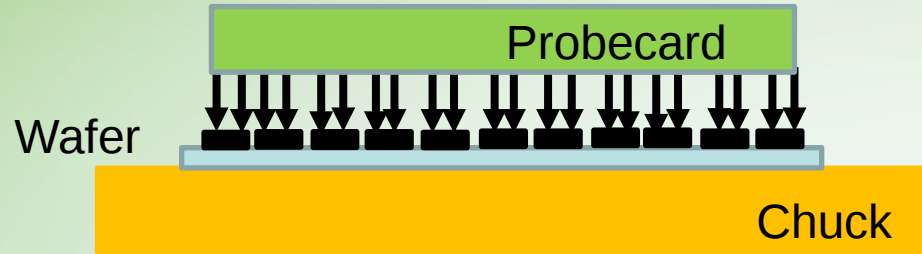
Interpretation of Data

- Uniform reaction on all 9 points inside the chuck within $\pm 2^{\circ}\text{C}$
- Uniform reaction of the extra sensor ($\approx$ DUT), however in a bigger range of about $\pm 5^{\circ}\text{C}$
- Thermal resistance between sensor / wafer / chuck is key to the data $\rightarrow$ thermal resistance between wafer and chuck is key to real measurement
- Average thermal resistance in this case is $(25^{\circ}\text{C} - 15^{\circ}\text{C}) / 150\text{W} = 0,07^{\circ}\text{C} / \text{W}$

Summary of High Wattage Chucks

- **Solution is provided for High Wattage device testing (CPU, GPU, etc...) up to:**
 - 600W per die
 - -60°C up to +150°C temperature range
 - 300 mm
- **Data proved:**
 - Same reaction independent from location
 - Fast adaption of chuck regarding power application
 - Uniform thermal resistance between chuck and wafer

Typical Full Wafer Contact (FWC) Test Set Up



- **Massive parallel contacting of many dies on the wafer up to full wafer contact**
- **Power is generated by many low power devices (e.g. $2048 \times 0,5W = 1024W$ thermal load)**
- **Products: DRAM, VCSEL, WLBI**

Thermal issues with FWC

- **The total amount of power can get very high, challenging at low temperatures**
- **Even with the strongest chiller, the heat exchange capabilities of the chuck is the bottleneck**
- **Good thermal uniformity is hard to achieve, especially non-operating dies are hard to predict**

Thermal Solution for FWC Test

- **New Heat Exchanger can allow very high power dissipation (up to 5kW)**
- **Special chuck design to deal with very high mechanical load**
- **Modular chiller concept to adapt to different applications**

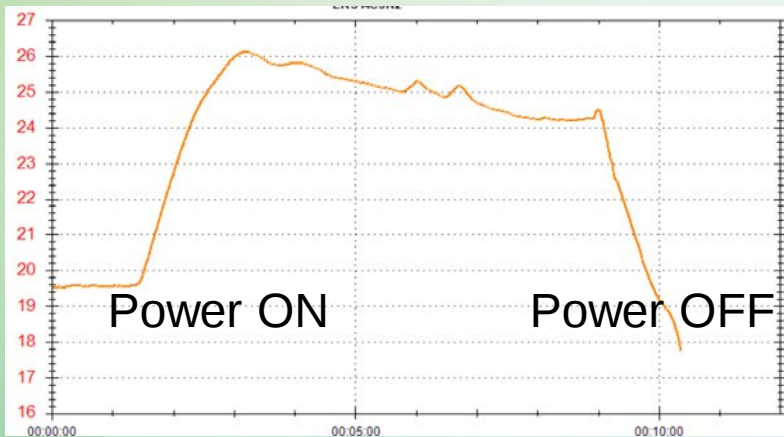
Test Set up for FWC Test

- 300mm heating device (up to 3kW) applied to a 300mm liquid chuck
- Temperature performance with different loadings and at different temperatures are performed

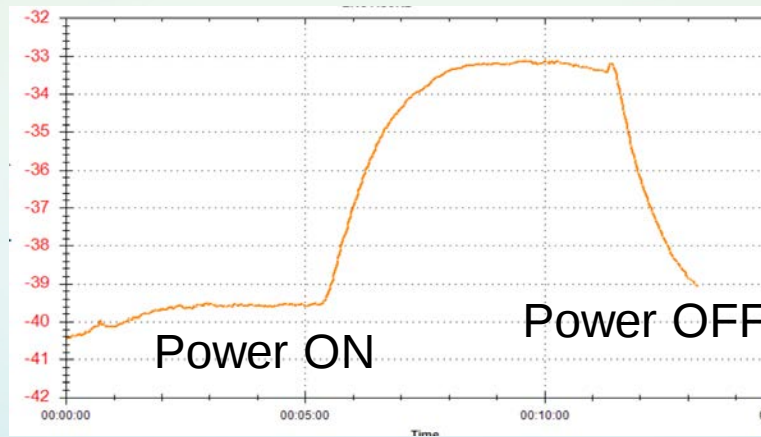


Data from FWC Test

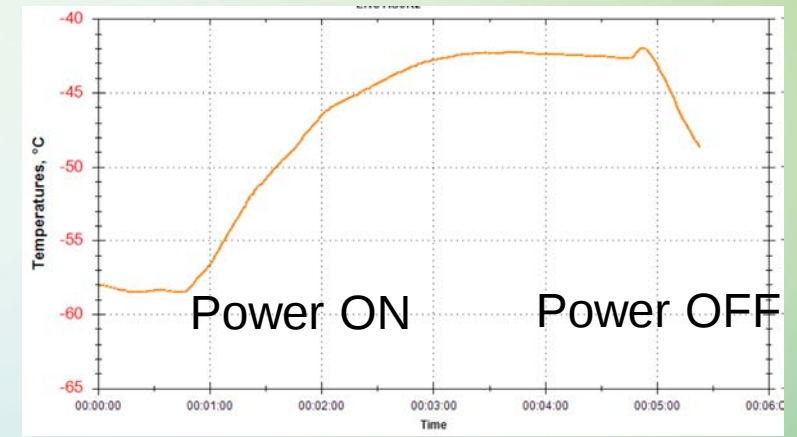
- 2,5kW applied at different temperatures
- Heat exchanger behaviour shown at different temperatures:



+20°C



- 40°C



- 60°C

→ 2,5kW dissipation for -40°C chuck temperature possible

Summary

- **All 3 „High Power“ scenarios come with thermal challenges**
- **Very different approaches are needed to solve the challenges**
- **Temperature offset of CDA pressurized probcards – can be addressed with ATCM**
- **Temperature uniformity at high wattage test – can be addressed with the special high wattage chuck**
- **Very High power dissipation at FWC – can be addressed with new heat exchanger and strong chiller, even at very low temperatures**

Outlook

- **Work to be done:**

- HV/HC Chucks:

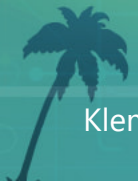
- > 400°C solution required
 - Lower leakage at elevated temperatures and voltages required

- High Wattage Chucks:

- Better control of the DUT required
 - Faster response time required

- FWC Chucks

- High power dissipation at elevated temperatures required
 - Better temperature uniformity required





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